

PATENT  
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Clews et al

Group No.: 1765

Serial No.: 10 / 010,850

Examiner: Tran, B.

Filed: December 5, 2001

Paper No.: 4

For: Selective Etchant for Oxide Sacrificial Material in Semiconductor Device Fabrication

**AMENDMENT AND RESPONSE TO OFFICE ACTION**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Applicants have carefully reviewed the Office Action of February 12, 2003 and submit the following in complete response thereto. Reconsideration of the claims and entry of the amendments presented herein is respectfully requested.

In the Claims

Please cancel Claim 10.

Please amend Claim 1 as follows:

- A. Sub
1. (Once Amended) A method for manufacturing a semiconductor device using an oxide sacrificial material, comprising the step of etching the oxide sacrificial material using an etching solution comprising hydrofluoric acid (HF) and sulfuric acid (H<sub>2</sub>SO<sub>4</sub>) in a ratio HF:H<sub>2</sub>SO<sub>4</sub> ranging from 1:1 to 3:1.

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GROUP 1700